



VOLTAGE RANGE: 50 - 1000V
CURRENT: 3.0 A

Features

- ! Glass Passivated Die Construction
- ! Ideally Suited for Automatic Assembly
- ! Low Forward Voltage Drop, High Efficiency
- ! Low Power Loss
- ! Ultra-Fast Recovery Time
- ! Plastic Case Material has UL Flammability Classification Rating 94V-O

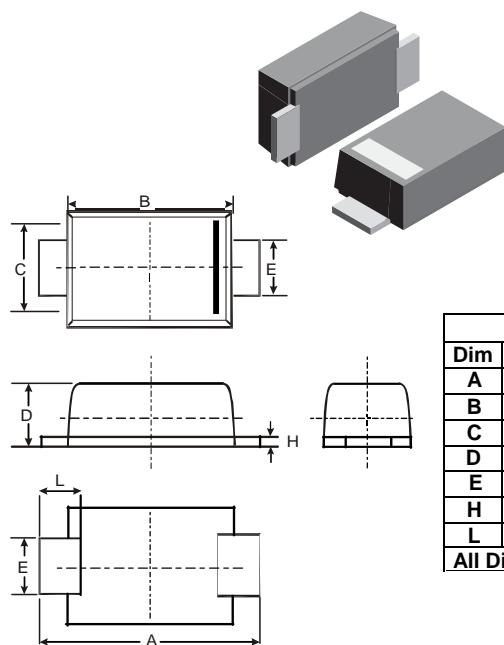
Mechanical Data

- ! Case:SMBF , Molded Plastic
- ! Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- ! Polarity: Cathode Band or Cathode Notch
- ! Marking: Type Number
- ! Weight: 0.0018 ounces,0.05grams



UF3AF - UF3MF

SURFACE MOUNT ULTRA FAST RECTIFIER DIODES



SMBF			
Dim	Min	Max	Typ
A	5.45	5.55	5.50
B	4.27	4.33	4.30
C	3.57	3.63	3.60
D	1.32	1.38	1.35
E	1.96	2.00	1.98
H	0.019	0.021	0.20
L	0.73	0.77	0.75
All Dimensions in mm			

Maximum Ratings and Electrical Characteristics $T_A = 25^\circ C$ unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	UF3AF	UF3BF	UF3DF	UF3GF	UF3JF	UF3KF	UF3MF	Unit				
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V				
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V				
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V				
Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=55^\circ C$	$I_{(AV)}$	3.0							A				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	100.0							A				
Maximum instantaneous forward voltage at 3.0A	V_F	1.0		1.30		1.70			V				
Maximum DC reverse current $T_A=25^\circ C$ at rated DC blocking voltage $T_A=100^\circ C$	I_R	5.0 250.0							μA				
Maximum reverse recovery time (NOTE 1)	t_{rr}	50		75					ns				
Typical junction capacitance (NOTE 2)	C_J	75							pF				
Typical thermal resistance (NOTE 3)	$R_{\theta JL}$	15.0							C/W				
Operating junction and storage temperature range	T_J, T_{STG}	-65 to +150							C				

Note: 1.Reverse recovery condition $I_F=0.5A, I_R=1.0A, I_{rr}=0.25A$

2.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3.The thermal resistance from junction to dead and from junction to ambient with P.C.B mounted on 0.3 x 0.3" (8.0 x 8.0 mm) Copper pad area

